

Attorney Docket No. P102-US

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

In re Application of: Patel, et al.

Art Unit: Not Yet Assigned

Serial No.: 10/627,155

Examiner: Not Yet Assigned

Filed: 7/24/03

For: **MICROMIRROR ARRAY DEVICE WITH A SMALL PITCH SIZE**

**INFORMATION DISCLOSURE STATEMENT**  
**PURSUANT TO 37 CFR 1.97(b)**

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-145

Sir:

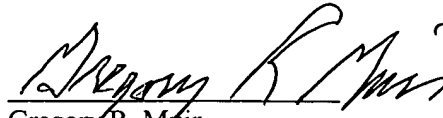
The attention of the Patent and Trademark Office is hereby directed to the documents listed on the attached PTO Form 1449. Copies of the cited references are enclosed.

No fee or certification is required in connection with this Information Disclosure Statement, since it is being submitted prior to the last of (1) issuance of a first official action on the merits and (2) expiration of the three month period following filing of the above-captioned application.

The above information is presented so that the Patent and Trademark Office can determine any materiality thereof to the claimed invention. It is respectfully requested that the information be considered during the prosecution of this application and that the cited documents be listed on the front page of any patent issuing from this application.

The Patent Office is authorized to charge our Deposit Account No. 501516 for any fee which it deems to be required to effect consideration of this statement.

Respectfully submitted,

A handwritten signature in black ink, appearing to read "Gregory R. Mair", written over a horizontal line.

Gregory R. Mair  
Attorney for Applicant(s)  
Registration No. 35,293

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		Application Number	10/627.155
<b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  (use as many sheets as necessary)		Filing Date	7/24/03
		First Named Inventor	Patel
		Art Unit	Not Yet Assigned
		Examiner Name	Not Yet Assigned
		Attorney Docket Number	P102-US
Sheet	1	of	6

U.S. PATENT DOCUMENTS					
Examiner Initials <sup>1</sup>	Cite No. <sup>1</sup>	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number - Kind Code <sup>2</sup> (if known)			
		US- 3,511,727	05-12-1970	Hays, R.G.	
		US- 4,190,488	02-26-1980	Winters, H.F.	
		US- 4,310,380	12-12-1982	Flamm et al.	
		US- 4,498,953	02-12-1985	Cook et al.	
		US- 6,051,503	04-18-2000	Bhardwai, J.K.	
		US- 6,436,229	08-20-2002	Tai et al.	
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		US- 6,355,181 B1	03-12-2002	McQuarrie, A.D.	
		US- 2001/0002663 A1	06-07-2001	Tai et al.	
		US- 5,439,553	08-08-1995	Grant et al.	
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		US- 2002/0196524 A1	12-26-2002	Huibers, et al.	
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		US- 5,726,480	03-10-1998	Pister, K.S.	
		US- 2002/0185699	12-12-2002	Reid	
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		US- 2002/0047172 A1	04-25-2002	Reid	
		US- 2003/0166342 A1	09/04/03	Chinn, et al.	

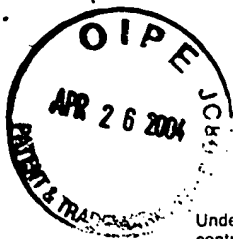
FOREIGN PATENT DOCUMENTS						
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		Country Code <sup>3</sup> -Number <sup>4</sup> - Kind Code <sup>5</sup> (if known)				
		EP-0704884-A2	04-03-1996	Mehta, J.		
		EP-0822582-A2	02-04-1998	Bhardwai, J.K.		
		EP-0822584-A2	04-04-1998	Bhardwai, J.K.		
		WO-99/49506	09-30-1999	McQuarrie, A.D.		
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		EP-0878824-A3	01-19-2000	McQuarrie et al.		
		JP-1982/57098679-A	06-18-1982	Tsunetoshi, A.		
		JP-1983/58130529-A	08-04-1983	Yoshihiro et al.		
		JP-1985/60057938-A	04-03-1985	Katsumi et al.		
		WO-98/32163	07-23-1998	Tai et al.		

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Sheet	2	of	6		

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		Number - Kind Code <sup>2</sup> (if known)			
		US- 6.409.876 B1	06-25-2002	McQuarrie, et al.	
		US- 6.396.619 B1	05-28-2002	Huibers, et al.	
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		US- 6.238.581	05-29-2001	Hawkins, et al.	
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		US- 2003/0071015 A1	04/17/03	Chinn, et al.	
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		US- 2003/0124848 A1	0703/03	Chinn, et al.	
		US- 2003/0219986 A1	11/27/03	Rattner, et al.,	
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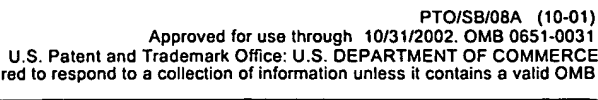
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		JP-1997/09251981-A	09-22-1997	Kazuaki et al.		
		JP-1998/10313128-A	11-24-1998	Hanmin et al.		
		JP-1998/10317169-A	12-02-1998	McQuarrie et al.		
		JP-1986/61187238-A	08-20-1986	Nobuo et al.		
		JP-1986/61270830-A	12-01-1986	Toru, T.		
		JP-1987/62071217-A	04-01-1987	Toru et al.		
		JP-1988/63155713-A	06-28-1988	Tadashi, F.		
		JP-1986/61053732-A	03-17-1986	Arata et al.		
		JP-1986/61134019-A	06-21-1986	Shinji et al.		
		JP-1986/61181131-A	08-13-1986	Shinji et al.		

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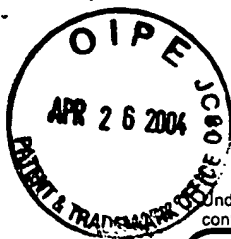
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<b>Application Number</b>	10/627,155
<b>Filing Date</b>	7/24/03
<b>First Named Inventor</b>	Patel
<b>Art Unit</b>	Not Yet Assigned
<b>Examiner Name</b>	Not Yet Assigned
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		<b>Group Art Unit</b>	Not Yet Assigned
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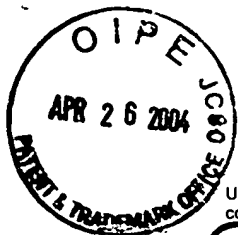
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		ALIEV et al., "Development of Si(100) Surface Roughness at the Initial Stage of Etching in F <sub>2</sub> and XeF <sub>2</sub> Gases Ellipsometric Study", Surface Science 442 (1999), pp. 206-214.	
		GLIDEMEISTER, J.M., "Xenon Difluoride Etching System" (Nov. 17, 1997).	
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		HECHT et al., "A Novel X-ray Photoelectron Spectroscopy Study of the Al/SiO <sub>2</sub> Interface", J. Appl. Phys. Vol. 57 (June 15, 1985), pp. 5256-5261.	
		HOULE, F.A., "Dynamics of SiF <sub>4</sub> Desorption During Etching of Silicon by XeF <sub>2</sub> ", IBM Almaden Research Center (April 15, 1987), pp. 1866-1872.	
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		VUGTS et al., "Si/XeF <sub>2</sub> Etching: Temperature Dependence", J. Vac. Sci. Technol. A 14(5) (Sep/Oct 1996), pp. 2766-2774.	
		WINTERS, H.F., "Etch Products from the Reaction of XeF <sub>2</sub> with SiO <sub>2</sub> , SiO <sub>3</sub> , Si <sub>3</sub> N <sub>4</sub> , SiC, and Si in the Presence of Ion Bombardment", J. Vac. Sci. Technol. B 1(4) (Oct/Dec 1983), pp. 927-931.	

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		Filing Date	7/24/03
		First Named Inventor	Patel
		Group Art Unit	Not Yet Assigned
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		Attorney Docket Number	P102-US
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OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS			
Examiner Initials <sup>2</sup>	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published	T <sup>2</sup>
		Kurt Williams, Etch Rates for Micromachining Processing-Part II, 2003 IEEE, Pgs 761-778, Journal of Microelectromechanical Systems, Vol. 12, No. 6, December 2003.	
		WINTERS et al., "The Etching of Silicon with XeF <sub>2</sub> Vapor", Appl. Phys. Letter, Vol. 34(1) (January 1, 1979), pp. 70-73.	
		XACTIX, Inc., Marketing Brochure (June 27, 1999).	
		"Xenon Difluoride Isotropic Etch System: Seeing is Believing", Surface Technology Systems Ltd. brochure, Newport, UK (date unknown).	
		CHU et al., "Controlled Pulse-Etching with Xenon Difluoride", International Solid State Sensors and Actuators Conference (Transducers '97), Chicago, IL, Vol. 1 (June 16 - 19, 1997), pp. 665-668 (abstract only).	
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		CHANG et al., "Gas-Phase Silicon Micromachining with Silicon Difluoride", Proceedings of the SPIE - The International Society for Optical Engineering, Vol. 2641 (1995), pp. 117-128 (abstract only).	

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		SEBEL et al., "Reaction Layer Dynamics in Ion-Assisted Si/XeF <sub>2</sub> Etching: Temperature Dependence", J. Vac. Sci. Technol. A, Vac. Surf. Films, Vol. 18, No. 6, (Nov. 2000), pp. 2759-2769 (abstract only).	
		SEBEL et al., "Silicon Etch Rate Enhancement by Traces of Metal", J. Vac. Sci. Technol. A, Vac. Surf. Films, Vol. 17, No. 3, (May/June 1999), pp. 755-762 (abstract only).	
		SUGANO et al., "Study on XeF <sub>2</sub> Pulse Etching Using Wagon Wheel Pattern", Proceedings of the 1999 International Symposium on Micromechanics and Human Science: Towards the New Century, Nagoya, Japan (Nov. 23 - 26, 1999), pp. 163-167 (abstract only).	
		WANG et al., "Gas-Phase Silicon Etching with Bromine Trifluoride", International Solid State Sensors and Actuators Conference (Transducers '97), Chicago, IL, Vol. 2 (June 16 - 19, 1997), pp. 1505-1508 (abstract only).	
		MUTHUKUMARAN et al., "Gas-Phase Xenon Difluoride Etching of Microsystems Fabricated Through the Mitel 1.5- $\mu$ m CMOS Process", Can. J. Electr. Comput. Eng. (Canada), Vol. 25, No. 1 (Jan. 2000), pp. 35-41 (abstract only).	
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		SEBEL et al., "Etching of Si Through a Thick Condensed XeF <sub>2</sub> Layer", J. Vac. Sci. Technol. A, Vac. Surf. Films, Vol. 18, No. 5 (Sept/Oct 2000), pp. 2090-2097 (abstract only).	

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